



SOT-23 Plastic-Encapsulate Transistors

BCV27 TRANSISTOR (NPN)

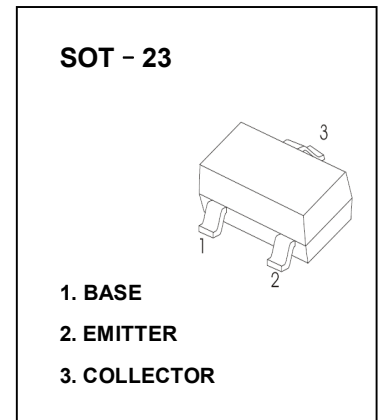
FEATURES

- High Collector Current
- High Current Gain

MARKING:FF

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current	500	mA
P_C	Collector Power Dissipation	300	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	416	$^\circ\text{C}/\text{W}$
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	10			V
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}, I_C=100\mu\text{A}$	4000			
	$h_{FE(2)}$	$V_{CE}=5\text{V}, I_C=10\text{mA}$	10000			
	$h_{FE(3)}$	$V_{CE}=5\text{V}, I_C=100\text{mA}$	20000			
	$h_{FE(4)}$	$V_{CE}=5\text{V}, I_C=0.5\text{A}$	4000			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}, I_B=0.1\text{mA}$			1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100\text{mA}, I_B=0.1\text{mA}$			1.5	V
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=50\text{mA}, f=100\text{MHz}$		170		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		3.5		pF